

49

32.

The method of claim 1, wherein forming a floating gate over a substrate comprises:

forming the inner first portion in contact with a gate dielectric;

and

forming the outer second portion atop the inner first portion.

43

33.

The method of claim 9, wherein forming a first layer comprises forming a first layer of conductively doped polysilicon in contact with a gate dielectric layer.

43

34.

The method of claim 25, wherein forming a first layer of poly silicon comprises forming a first layer of polysilicon in contact with a gate dielectric layer.

Full
1.126

Sub
E1

C1

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23